

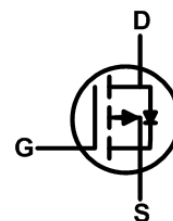
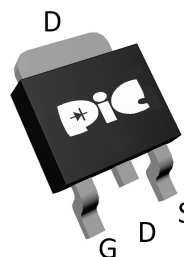
### ➤ General Description

This PAP41TX15X P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent  $R_{DS(ON)}$  performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

### ➤ Feature

- Super Low Gate Charge
- 100% EAS Guaranteed
- Green Device Available
- Excellent  $CdV/dt$  effect decline
- Advanced high cell density Trench technology

### ➤ TO-252



### ➤ Application

- Switch application
- DC/DC Converters Power
- Tools

### ➤ Absolute Maximum Ratings

| Parameter                                             | Symbol                | Rating     | Units        |
|-------------------------------------------------------|-----------------------|------------|--------------|
| Drain-Source Voltage                                  | $V_{DS}$              | -40        | V            |
| Gate-Source Voltage                                   | $V_{GS}$              | $\pm 20$   | V            |
| Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup> | $I_D@T_C=25^\circ C$  | -52        | A            |
| Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup> | $I_D@T_C=100^\circ C$ | -32        | A            |
| Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup> | $I_D@T_A=25^\circ C$  | -10        | A            |
| Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup> | $I_D@T_A=70^\circ C$  | -8         | A            |
| Pulsed Drain Current <sup>2</sup>                     | $I_{DM}$              | -105       | A            |
| Single Pulse Avalanche Energy <sup>3</sup>            | EAS                   | 146        | mJ           |
| Avalanche Current                                     | $I_{AS}$              | -54        | A            |
| Total Power Dissipation <sup>4</sup>                  | $P_D@T_C=25^\circ C$  | 52.1       | W            |
| Total Power Dissipation <sup>4</sup>                  | $P_D@T_A=25^\circ C$  | 2          | W            |
| Storage Temperature Range                             | $T_{STG}$             | -55 to 150 | $^\circ C$   |
| Operating Junction Temperature Range                  | $T_J$                 | -55 to 150 | $^\circ C$   |
| Thermal Resistance Junction-Ambient <sup>1</sup>      | $R_{\theta JA}$       | 62         | $^\circ C/W$ |
| Thermal Resistance Junction-Case <sup>1</sup>         | $R_{\theta JC}$       | 2.4        | $^\circ C/W$ |

### ➤ Electrical Characteristics ( $T_J=25^\circ C$ Unless otherwise noted)

| Parameter                                      | Symbol                       | Conditions                                                     | Min. | Typ.   | Max.      | Unit          |
|------------------------------------------------|------------------------------|----------------------------------------------------------------|------|--------|-----------|---------------|
| Drain-Source Breakdown Voltage                 | $BV_{DSS}$                   | $V_{GS}=0V$ , $I_D=-250\mu A$                                  | -40  | ---    | ---       | V             |
| $BV_{DSS}$ Temperature Coefficient             | $\Delta BV_{DSS}/\Delta T_J$ | Reference to $25^\circ C$ , $I_D=-1mA$                         | ---  | -0.023 | ---       | $V/^\circ C$  |
| Static Drain-Source On-Resistance <sup>2</sup> | $R_{DS(ON)}$                 | $V_{GS}=-10V$ , $I_D=-18A$                                     | ---  | 10.5   | 13        | $m\Omega$     |
|                                                |                              | $V_{GS}=-4.5V$ , $I_D=-12A$                                    | ---  | 15     | 20        |               |
| Gate Threshold Voltage                         | $V_{GS(th)}$                 | $V_{GS}=V_{DS}$ , $I_D=-250\mu A$                              | -1.0 | -1.6   | -2.5      | V             |
| $V_{GS(th)}$ Temperature Coefficient           | $\Delta V_{GS(th)}$          |                                                                | ---  | 4.74   | ---       | $mV/^\circ C$ |
| Drain-Source Leakage Current                   | $I_{DSS}$                    | $V_{DS}=-32V$ , $V_{GS}=0V$ , $T_J=25^\circ C$                 | ---  | ---    | 1         | $\mu A$       |
|                                                |                              | $V_{DS}=-32V$ , $V_{GS}=0V$ , $T_J=55^\circ C$                 | ---  | ---    | 5         |               |
| Gate-Source Leakage Current                    | $I_{GSS}$                    | $V_{GS}=\pm 20V$ , $V_{DS}=0V$                                 | ---  | ---    | $\pm 100$ | nA            |
| Forward Transconductance                       | $g_{fs}$                     | $V_{DS}=-5V$ , $I_D=-18A$                                      | ---  | 24     | ---       | S             |
| Gate Resistance                                | $R_g$                        | $V_{DS}=0V$ , $V_{GS}=0V$ , $f=1MHz$                           | ---  | 7      | 14        | $\Omega$      |
| Total Gate Charge (-4.5V)                      | $Q_g$                        | $V_{DS}=-20V$ , $V_{GS}=-4.5V$ , $I_D=-12A$                    | ---  | 27.9   | ---       | nC            |
| Gate-Source Charge                             | $Q_{gs}$                     |                                                                | ---  | 7.7    | ---       |               |
| Gate-Drain Charge                              | $Q_{gd}$                     |                                                                | ---  | 7.5    | ---       |               |
| Turn-On Delay Time                             | $T_{d(on)}$                  | $V_{DD}=-15V$ , $V_{GS}=-10V$ , $R_G=3.3\Omega$ ,<br>$I_D=-1A$ | ---  | 40     | ---       | ns            |
| Rise Time                                      | $T_r$                        |                                                                | ---  | 35.2   | ---       |               |
| Turn-Off Delay Time                            | $T_{d(off)}$                 |                                                                | ---  | 100    | ---       |               |
| Fall Time                                      | $T_f$                        |                                                                | ---  | 9.6    | ---       |               |
| Input Capacitance                              | $C_{iss}$                    | $V_{DS}=-15V$ , $V_{GS}=0V$ , $f=1MHz$                         | ---  | 3500   | ---       | pF            |
| Output Capacitance                             | $C_{oss}$                    |                                                                | ---  | 323    | ---       |               |
| Reverse Transfer Capacitance                   | $C_{rss}$                    |                                                                | ---  | 222    | ---       |               |

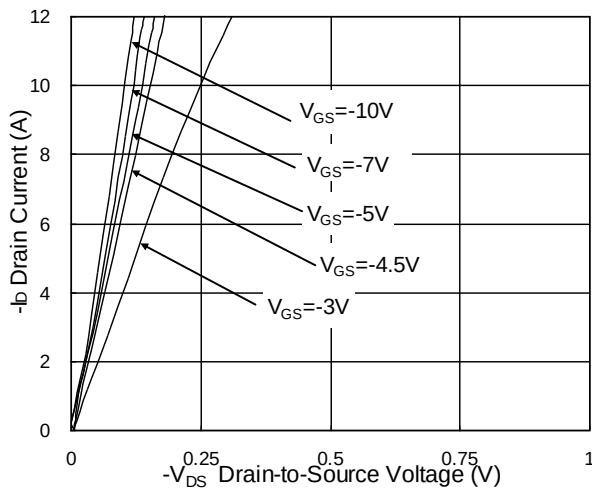
### ➤ Diode Characteristics

| Parameter                                | Symbol   | Conditions                                 | Min. | Typ. | Max. | Unit |
|------------------------------------------|----------|--------------------------------------------|------|------|------|------|
| Continuous Source Current <sup>1,5</sup> | $I_S$    | $V_G=V_D=0V$ , Force Current               | ---  | ---  | -52  | A    |
| Pulsed Source Current <sup>2,5</sup>     | $I_{SM}$ |                                            | ---  | ---  | -105 | A    |
| Diode Forward Voltage <sup>2</sup>       | $V_{SD}$ | $V_{GS}=0V$ , $I_S=-1A$ , $T_J=25^\circ C$ | ---  | ---  | -1   | V    |

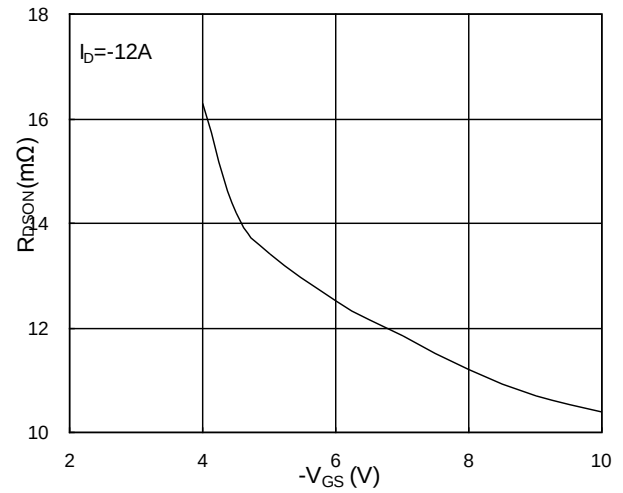
Note :

1. Pulse width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
3. The EAS data shows Max. rating. The test condition is  $V_{DD}=-25V$ ,  $V_{GS}=-10V$ ,  $L=0.1mH$ ,  $I_{AS}=-54A$
4. Ensure that the channel temperature does not exceed  $150^\circ C$ .
5. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.

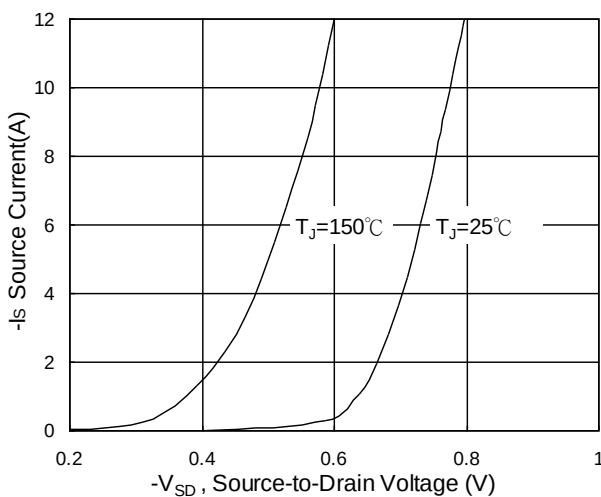
### ➤ Typical Characteristics



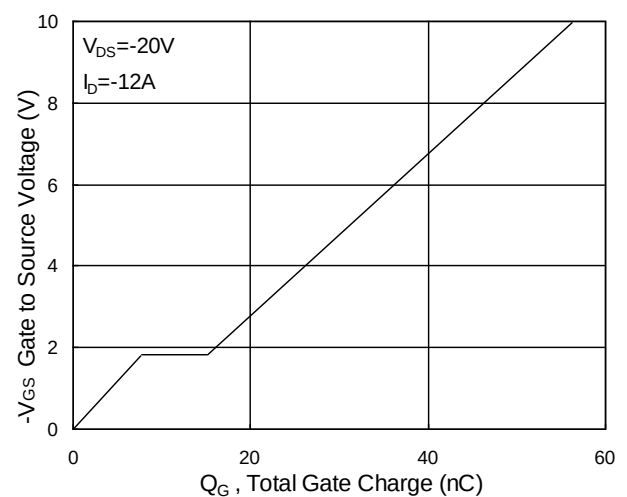
**Fig.1 Typical Output Characteristics**



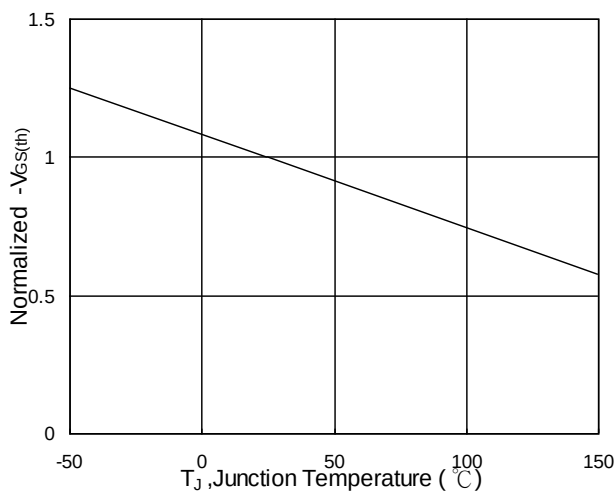
**Fig.2 On-Resistance v.s Gate-Source**



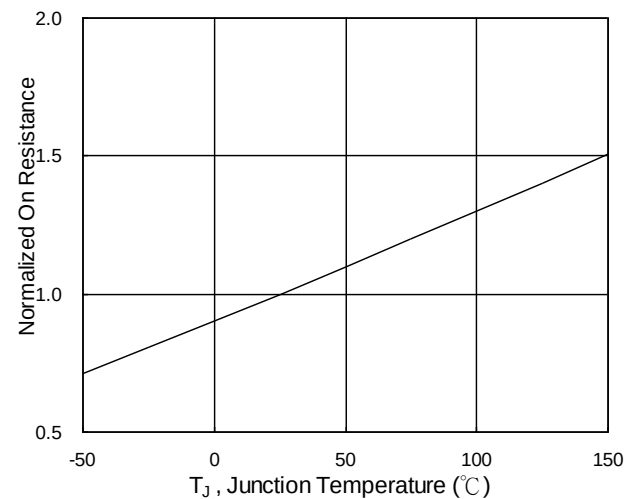
**Fig.3 Forward Characteristics Of Reverse**



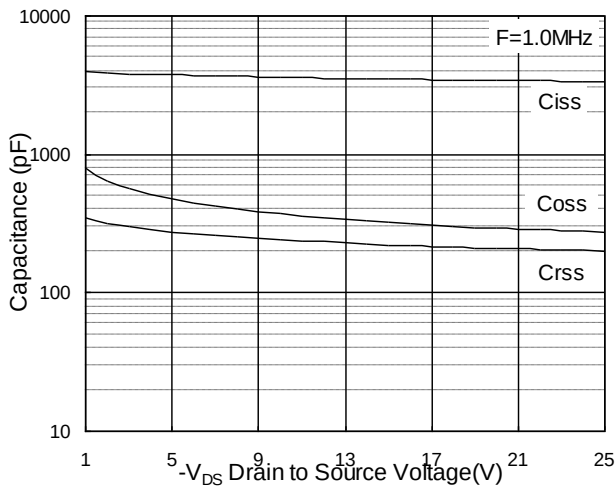
**Fig.4 Gate-Charge Characteristics**



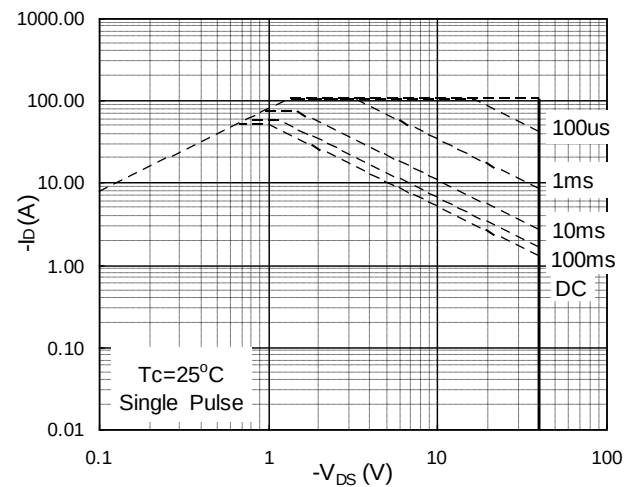
**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$**



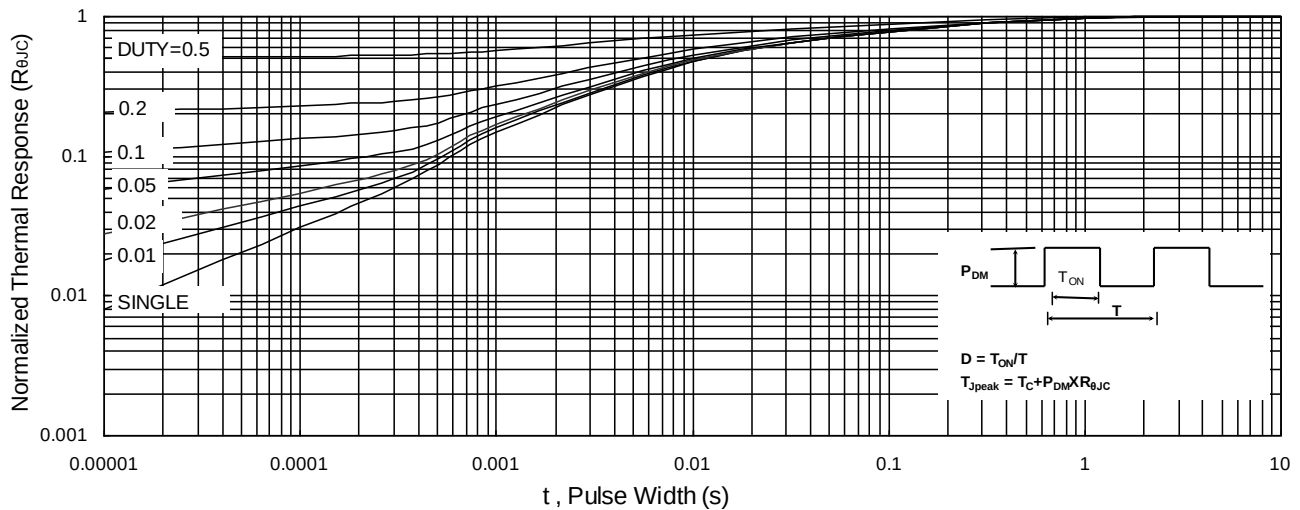
**Fig.6 Normalized  $R_{DS(ON)}$  v.s  $T_J$**



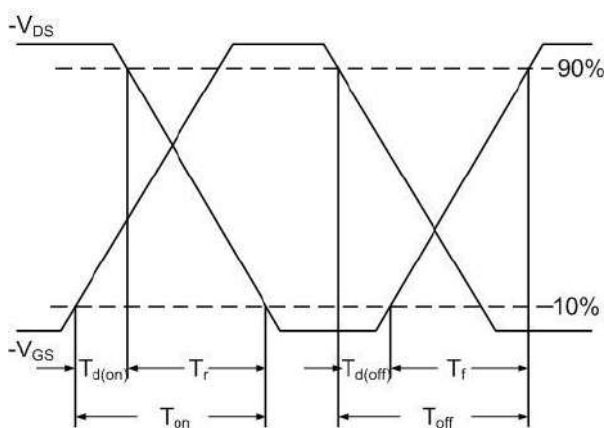
**Fig.7 Capacitance**



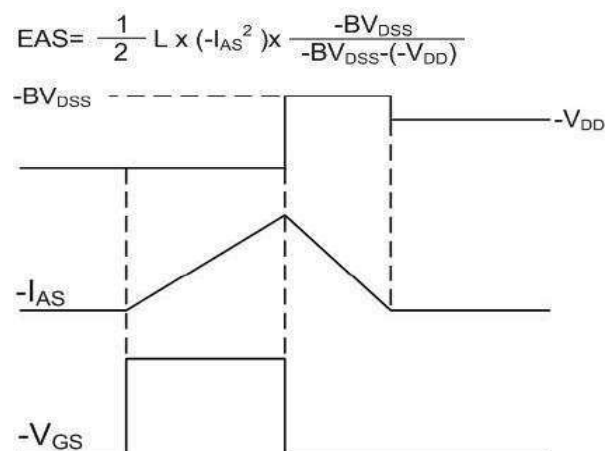
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

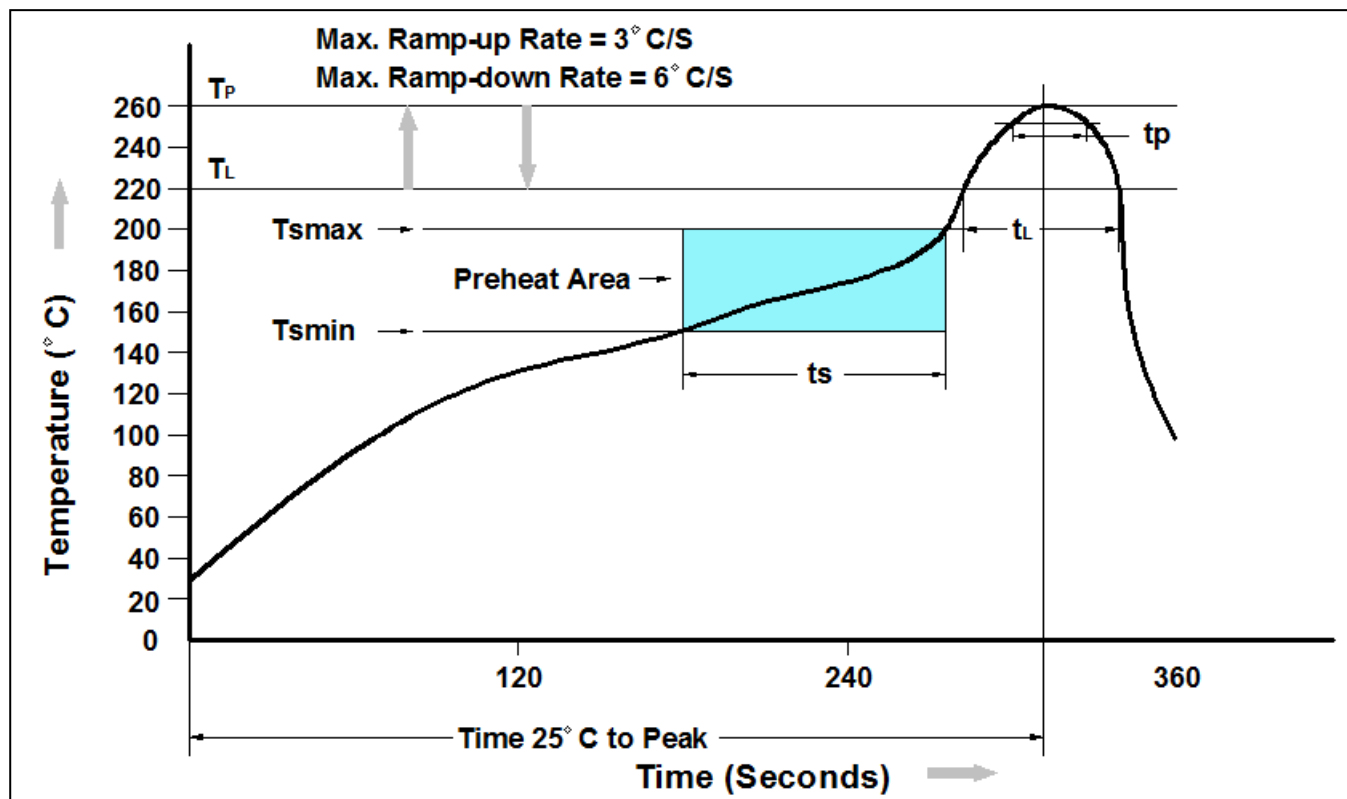


**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Waveform**

## ➤ Recommend IR Reflow Soldering Thermal Profile

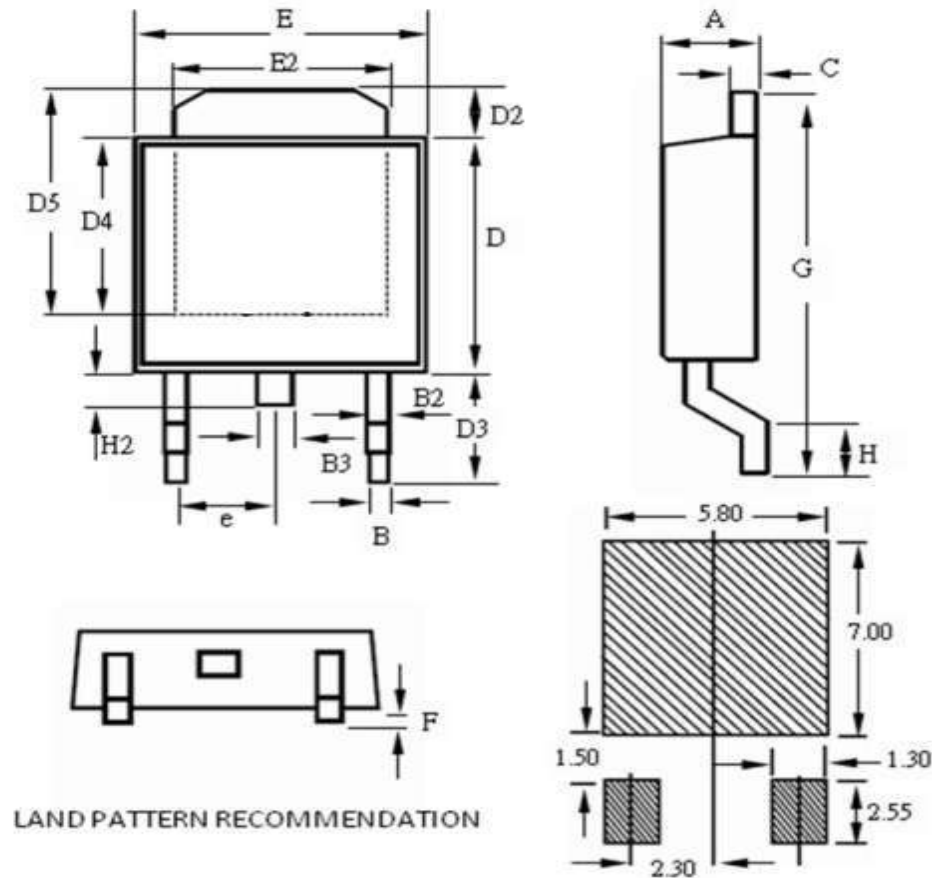


| Profile Feature                                      | Pb-Free Assembly Profile |
|------------------------------------------------------|--------------------------|
| Temperature Min. ( $T_{smin}$ )                      | 150°C                    |
| Temperature Max. ( $T_{smax}$ )                      | 200°C                    |
| Time ( $t_s$ ) from ( $T_{smin}$ to $T_{smax}$ )     | 60-120 seconds           |
| Average Ramp-up Rate ( $t_L$ to $t_P$ )              | 3°C/second max.          |
| Liquidous Temperature ( $T_L$ )                      | 217°C                    |
| Time ( $t_L$ ) Maintained Above ( $T_L$ )            | 60 – 150 seconds         |
| Peak Temperature                                     | 260°C +0°C / -5°C        |
| Time ( $t_P$ ) within 5°C of actual Peak Temperature | 30 seconds               |
| Ramp-down Rate ( $T_P$ to $T_L$ )                    | 6°C/second max           |
| Time 25°C to Peak Temperature                        | 8 minutes max.           |

## ➤ Ordering Information

| Part Number | Description | Quantity |
|-------------|-------------|----------|
| PAP41TX15X  | TO-252 Reel | 2500 pcs |

## ➤ Package Information ( TO-252 )



| SYMBOLS | MILLIMETERS |      |       | INCHES |       |       |
|---------|-------------|------|-------|--------|-------|-------|
|         | MIN         | NOM  | MAX   | MIN    | NOM   | MAX   |
| A       | 2.10        | --   | 2.50  | 0.083  | --    | 0.098 |
| B       | 0.30        | --   | 0.89  | 0.012  | --    | 0.035 |
| B2      | 0.40        | --   | 1.14  | 0.016  | --    | 0.045 |
| B3      | 0.60        | --   | 1.00  | 0.024  | --    | 0.039 |
| C       | 0.40        | --   | 0.89  | 0.016  | --    | 0.035 |
| D       | 5.30        | --   | 6.25  | 0.209  | --    | 0.246 |
| D2      | 0.50        | --   | 1.70  | 0.020  | --    | 0.067 |
| D3      | 2.20        | --   | 3.40  | 0.087  | --    | 0.134 |
| D4      | 4.32        | --   | --    | 0.170  | --    | --    |
| D5      | 5.21        | --   | --    | 0.205  | --    | --    |
| E       | 6.30        | --   | 6.73  | 0.248  | --    | 0.265 |
| E2      | 4.80        | --   | 5.46  | 0.189  | --    | 0.215 |
| F       | 0.00        | --   | 0.30  | 0.000  | --    | 0.012 |
| G       | 9.20        | --   | 10.41 | 0.362  | --    | 0.410 |
| H       | 0.90        | --   | 1.95  | 0.035  | --    | 0.077 |
| H2      | 0.50        | --   | 1.10  | 0.020  | --    | 0.043 |
| e       | --          | 2.30 | --    | --     | 0.091 | --    |

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